

Amendments to the Specification:

Please replace the paragraph beginning at page 6, line 3, with the following amended paragraph:

A mesa between trenches 306 includes a P-body region 316. Within P-body region 316 are N+ source regions 312 and a P+ body contact region 314. The top surface of gate 308 is covered with a BPSG layer 324. A source metal layer 326 ~~326S~~ overlies BPSG layer 324 and makes electrical contact with N+ source regions 312 and P+ body contact regions 314. Similarly, a metal layer 325 contacts N+ substrate 302, which functions as the drain. The electrical contact between metal layer 325 and N+ substrate 302 could be ohmic or could include a Schottky barrier.

Please replace the paragraph beginning at page 7, line 8, with the following amended paragraph:

Each of field shield regions 320 is connected to P-body regions 316 and N+ source regions 312 in the third dimension, outside the plane of the drawing. **Figs. 3A and 3B** illustrate how this can be done. **Fig. 3A** is a cross-sectional view taken at the end of one of trenches 306 showing how field shield regions 320 can be connected to P-body regions 316 and N+ source regions 312. A P-well 328 is formed by ion implantation through a mask and diffusing a P-type dopant such as boron at the ends of trenches 306. As the P-type dopant diffuses, the P-well expands laterally under the sidewall spacers 322 and merges with the field shield regions 320. A P+ contact region 330 is formed beneath an opening in BPSG layer 324 at the surface of epi layer 304 to form an ohmic contact with metal layer 326 ~~326S~~. P+ contact region 330 can be formed during the same process step as P+ body contact region 314, shown in **Fig. 2**. Since metal layer 326 ~~326S~~ is in electrical contact with N+ source regions 312 and P+ body contact regions 314 (see **Fig. 2**), field shield regions 320 are likewise in electrical contact with N+ source regions 312 and P+ body contact regions 314.

Please replace the paragraph beginning at page 7, line 22, with the following amended paragraph:

Field shield regions 320 can also be connected to N+ source regions 312 and P+ body contact regions 314 by means of a wide trench, as shown in **Fig. 3B**. Wide trench

602 is an extension of trench 306 and may be located at the end of each rectangular trench cell, for example. At the bottom of trench 602 is a P shield region 604, which is an extension of field shield region 320. Also included in trench 602 are polysilicon spacers 606, BPSG spacers 610, and a metal plug 612. Metal plug 612 extends downward from metal layer 326 ~~326S~~. A P+ region 608 within P shield region 604 provides an ohmic contact with metal slug 612. Therefore, since P shield region 604 is an extension of field shield region 320, and since metal layer 326 ~~326S~~ is in electrical contact with N+ source regions 312 and P+ body contact regions 314, this structure forms an electrical link between field shield region 320 and both N+ source regions 312 and P+ body contact regions 314.